Abstracts

10 GHz-10 W Internally Matched Flip-Chip GaAs Power FETs (1980 [MWSYM])

Y. Mitsui, M. Kobiki, M. Wataze, K. Segawa, M. Otsubo, M. Nakatani and T. Ishii. "10 GHz-10 W Internally Matched Flip-Chip GaAs Power FETs (1980 [MWSYM])." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 6-8.

The flip-chip GaAs power f.e.t. delivering 10 W power output with 3 dB gain has been realized at 10 GHz by using a newly developed internal matching technique, in which the f.e.t. chips are directly connected to the lumped dielectric capacitors prepared for the matching networks.

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